

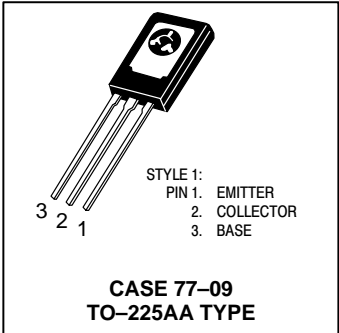
# Plastic Medium Power PNP Silicon Transistor

... designed for use in line-operated applications such as low power, line-operated series pass and switching regulators requiring PNP capability.

- High Collector–Emitter Sustaining Voltage —  
 $V_{CEO(sus)} = 300 \text{ Vdc @ } I_C = 1.0 \text{ mAdc}$
- Excellent DC Current Gain —  
 $h_{FE} = 30\text{--}240 \text{ @ } I_C = 50 \text{ mAdc}$
- Plastic Thermopad Package

**MJE350**

**0.5 AMPERE  
POWER TRANSISTOR  
PNP SILICON  
300 VOLTS  
20 WATTS**



### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO}$	300	Vdc
Emitter–Base Voltage	$V_{EB}$	3.0	Vdc
Collector Current — Continuous	$I_C$	500	mAdc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	20 0.16	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$\theta_{JC}$	6.25	$^\circ\text{C/W}$

### ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Collector–Emitter Sustaining Voltage ( $I_C = 1.0 \text{ mAdc}, I_B = 0$ )	$V_{CEO(sus)}$	300	—	Vdc
Collector Cutoff Current ( $V_{CB} = 300 \text{ Vdc}, I_E = 0$ )	$I_{CBO}$	—	100	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = 3.0 \text{ Vdc}, I_C = 0$ )	$I_{EBO}$	—	100	$\mu\text{Adc}$
<b>ON CHARACTERISTICS</b>				
DC Current Gain ( $I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ )	$h_{FE}$	30	240	—

# MJE350

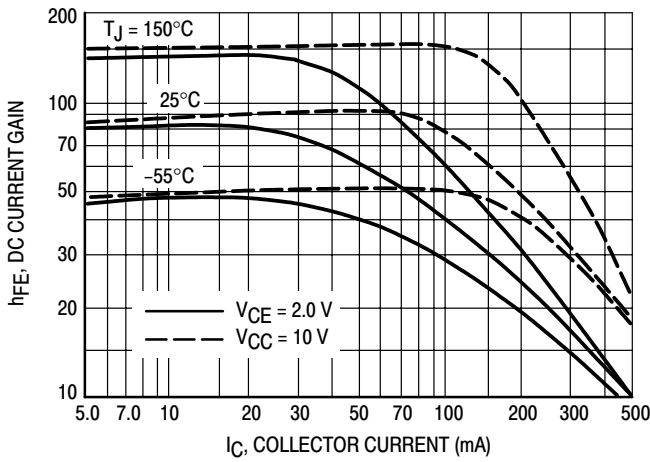


Figure 1. DC Current Gain

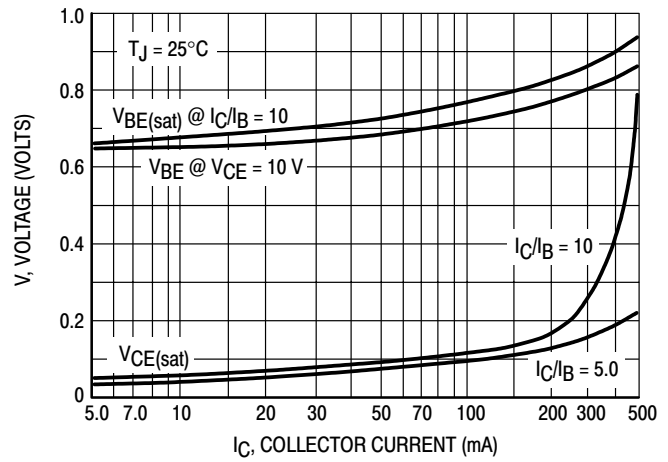


Figure 2. "On" Voltages

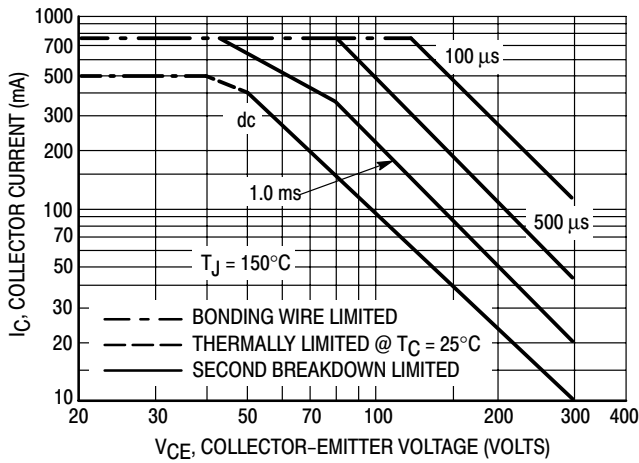


Figure 3. Active-Region Safe Operating Area

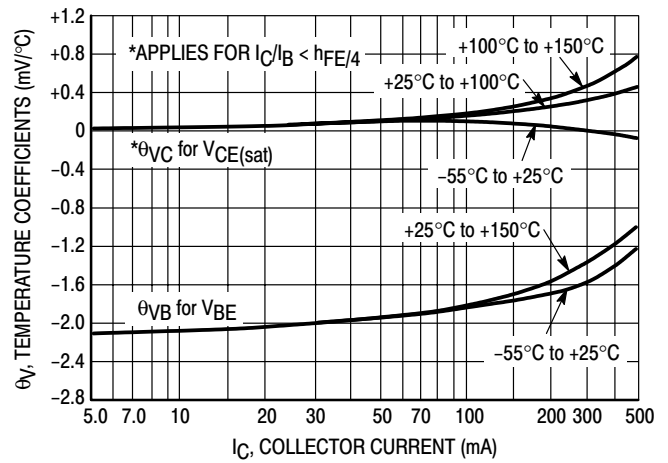


Figure 4. Temperature Coefficients

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 3 is based on  $T_{J(pk)} = 150^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(pk)} \leq 150^\circ\text{C}$ . At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

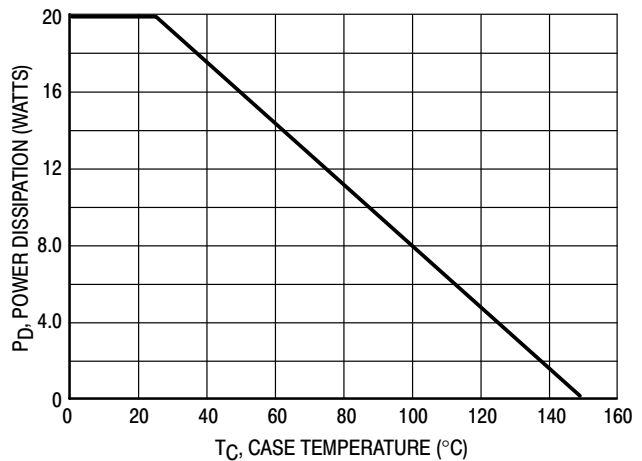
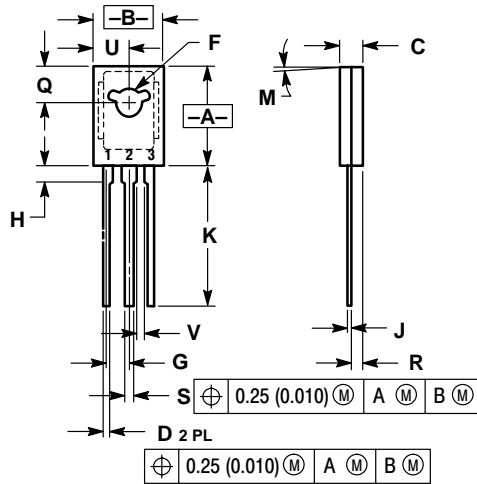


Figure 5. Power Derating

# MJE350

## PACKAGE DIMENSIONS


### TO-225 CASE 77-09 ISSUE W



- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	----	1.02	----

- STYLE 1:  
 PIN 1. EMITTER  
 2. COLLECTOR  
 3. BASE

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